

BD410

NPN EPITAXILA SILICON POWER TRANSISTORS

They are silicon epitaxial planar NPN power transistors mounted in a TO-126 plastic package. AF-amplifier for high supply voltage

They are intended for control circuit, vertical output stages in TVsets, and general purpose applications.

Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit
V _{CBO}	Collector-Base Voltage	500	V	
V _{CEO}	Collector-Emitter Voltage	325	V	
V _{EBO}	Emitter-Base Voltage	5	V	
Ic	Collector Current		1	А
I _{CM}	Collector Peak Current		1.5	А
P _T	Total Power Dissipation	$T_a = 25$ °C $T_c = 25$ °C	1.25 20	W
t J	Junction Temperature		-55 to +125	
t s	Storage Temperature range		-55 to +125	°C
t L	Lead Temperature 1.6 mm From Case For 10 Secondes		260	



BD410

ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise noted

TC-20 O diffess otherwise noted						
Symbol	Ratings	Test Condition(s)	Min	Тур	Max	Unit
V _{CEO}	Collector-Emitter Breakdown Voltage (*)	I _C = 10 mA, I _B = 0	325	-	-	V
V _{CBO}	Collector-Base Breakdown Voltage	I_{C} = 0.5 mA, I_{E} = 0	500	-	-	V
V _{EBO}	Collector-Base Breakdown Voltage	I _E = 50 μA, I _C = 0	5	-	-	V
I _{CES}	Collector Cutoff Current	V _{CE} = 300 V, I _B = 0	-	-	100	μΑ
V _{CE(SAT)}	Collector-Emitter saturation Voltage (*)	I _C = 100 mA, I _B = 10 mA	-	-	0.5	V
V _{BE}	Base-Emitter Voltage (*)	I _C = 100 mA, I _B = 10 mA	-	-	1.5	٧
		I _C = 5 mA, V _{CE} = 10 V	25	-	-	
h _{FE}	DC Current Gain (*)	I _C = 50 mA, V _{CE} = 10 V	30	-	240	-
		I _C = 100 mA, V _{CE} = 10 V	20	-	-	

SWITCHING TIMES.

Symbol	Ratings	Test Condition(s)	Min	Тур	Mx	Unit
C _{obo}	Output Capacitance	I _E = 0, V _{CB} = 10 V, f= 1 MHz	-	5.5	-	pF
C _{ibo}	Input Capacitance	I _E = 0, V _{CB} = 0.5 V, f= 1 MHz	_	90	-	ρΓ

^(*) These parameters must be measured using pulse techniques, t_p 300 $\mu s,$ Duty Cycle \angle 2%

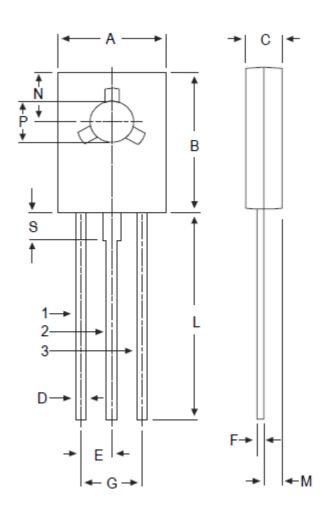


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MECHANICAL DATA CASE TO-126

	DIMENSIONS		
	min	max	
Α	7.4	7.8	
В	10.5	10.8	
С	2.4	2.7	
D	0.7	0.9	
Е	2.25 typ.		
F	0.49	0.75	
G	4.4 typ.		
L	15.7 typ.		
М	1.27 typ.		
N	3.75 typ.		
Р	3.0	3.2	
S	2.54	typ.	

Pin 1 :	Emitter
Pin 2 :	Collector
Pin 3 :	Base



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